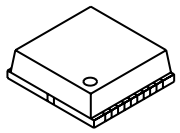
SONY

CXG1134EN

High Power SPDT Switch with Logic Control

10 pin VSON (Plastic)



Description

The CXG1134EN is a high power and high Isolation SPDT switch MMIC. This IC can be used in wireless communication systems. The CXG1134EN can be operated by one CMOS control line. The Sony GaAs J-FET process is used for low insertion loss and on-chip logic circuit.

Features

- Low insertion loss: 0.25dB @900MHz,
  0.35dB @1.9GHz
- High linearity: IIP3 (typ.) = 70dBm
- 1 CMOS compatible control line
- Small package size: 10-pin VSON

Applications

- Cellular handsets
- PDC, CDMA

Structure

GaAs J-FET MMIC

Absolute Maximum Ratings (Ta = 25°C)

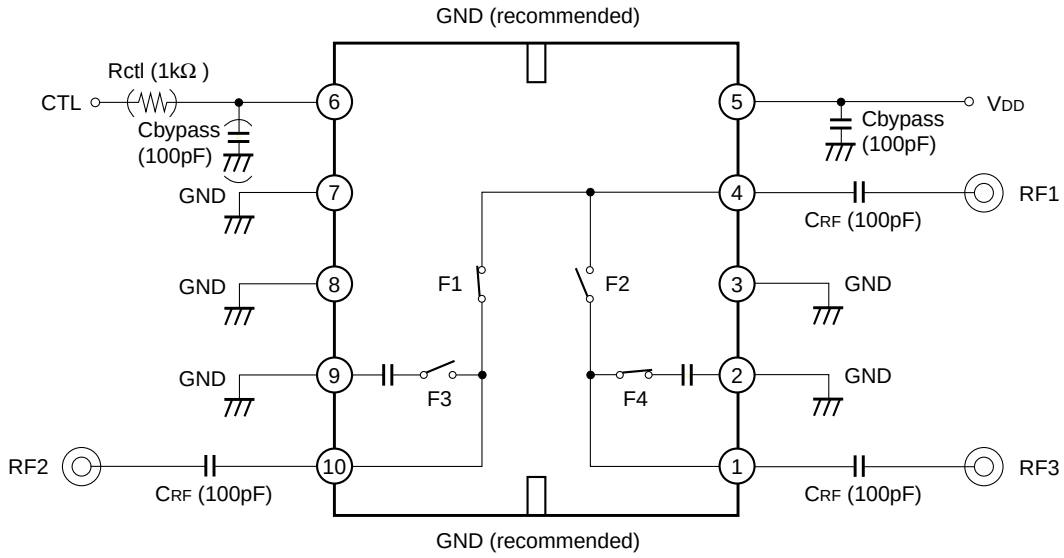
• Bias voltage	V_{DD}	7	V
• Control voltage	Vctl	5	V
• Operating temperature	Topr	–35 to +85	°C
• Storage temperature	Tstg	–65 to +150	°C

GaAs MMICs are ESD sensitive devices. Special handling precautions are required.

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E02330-PS

Block Diagram and Recommended Circuit



When using this IC, the following external parts should be used:

Rctl: This resistor is used to improve ESD performance. 1kΩ is recommended.

C_{RF}: This capacitor is used for RF de-coupling and must be used for all applications. 100pF is recommended.

Cbypass: This capacitor is used for DC line filtering. 100pF is recommended.

Truth Table

On Pass	CTL	F1	F2	F3	F4
RF1 – RF2	H	ON	OFF	OFF	ON
RF1 – RF3	L	OFF	ON	ON	OFF

DC Bias Condition

(Ta = 25°C)

Item	Min.	Typ.	Max.	Unit
Vctl (H)	2.2	3.0	3.6	V
Vctl (L)	0	—	0.4	V
V_{DD}	2.7	3.0	3.6	V

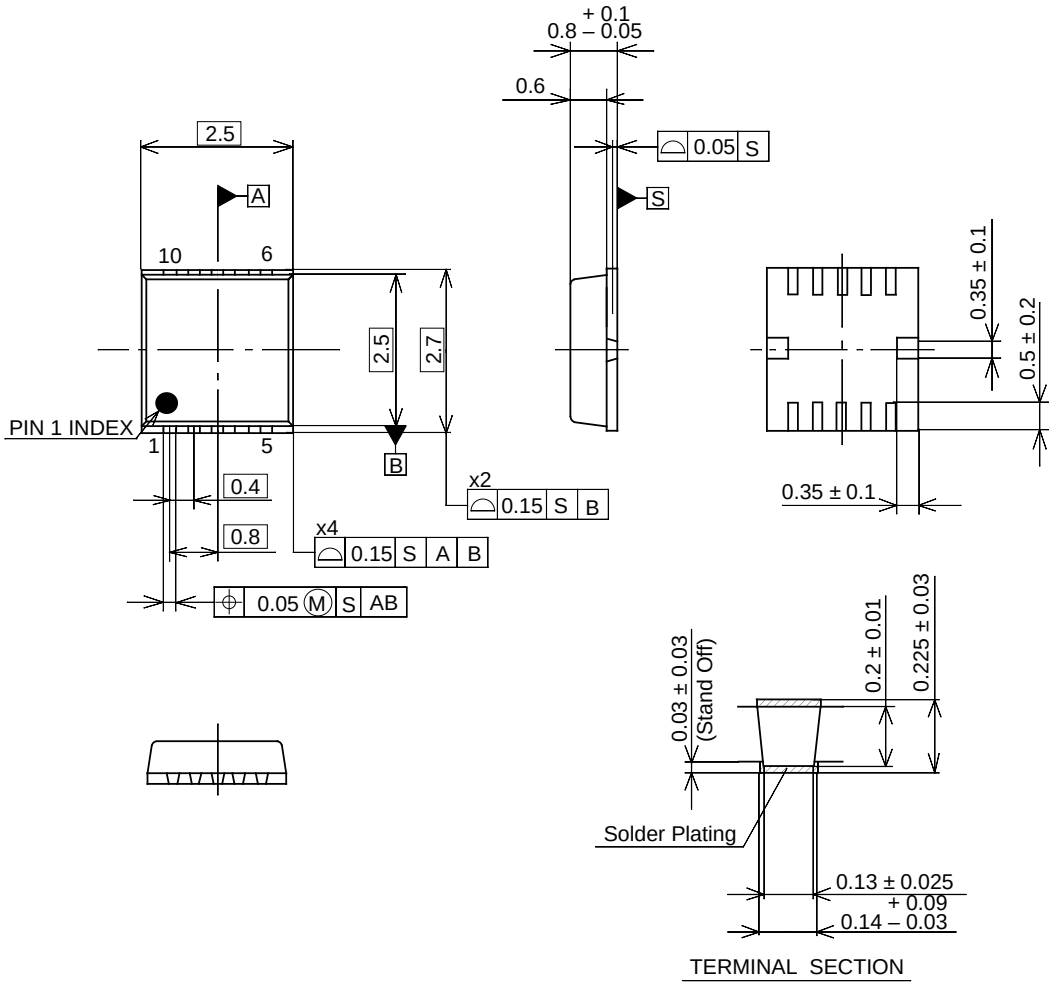
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Insertion loss	IL	900MHz		0.25	0.50	dB
Isolation	ISO.	900MHz	28	32		dB
VSWR	VSWR	900MHz		1.2	1.4	—
Harmonics	2fo	*1		–75	–60	dBc
	3fo	*1		–75	–60	dBc
1dB compression input power	P1dB	V_{DD} = 3.0V, 0/3V control	32	35		dBm
Switching speed	TSW			2	5	µs
Control current	Ictl	Vctl (High) = 3V		10	30	µA
Bias current	I_{DD}	V_{DD} = 3V		50	100	µA

*1 Pin = 30dBm, 900MHz, V_{DD} = 3.0V, 0/3V control

Package Outline Unit: mm

10PIN VSON(PLASTIC)



NOTE: 1) The dimensions of the terminal section apply to the ranges of 0.1mm and 0.25mm from the end of a terminal.

SONY CODE	VSON-10P-01
EIAJ CODE	————
JEDEC CODE	————

PACKAGE STRUCTURE

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	0.013g

LEAD PLATING SPECIFICATIONS

ITEM	SPEC.
LEAD MATERIAL	COPPER ALLOY
SOLDER COMPOSITION	Sn-Bi Bi:1-4wt%
PLATING THICKNESS	5-18µm